

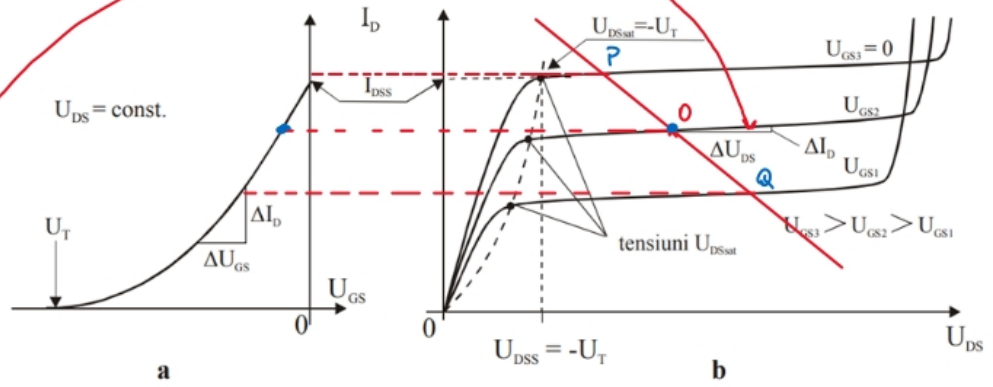
Seminar 5

Amplificatoare cu JFET:

Param. AC:

$$g_m = \left(\frac{\Delta I_D}{\Delta U_{GS}} \right)_{U_{DS} = ct.}$$

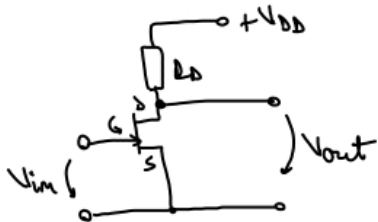
$$r_d = \left(\frac{\Delta U_{DS}}{\Delta I_D} \right)_{U_{GS} = ct.}$$



În datasheet: $|Y_{fs}| = g_m$
 $|Y_{os}| = \frac{1}{r_d}$

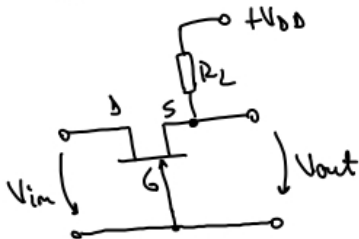
Conexiuni ale JFET:

1) Sursă comună:

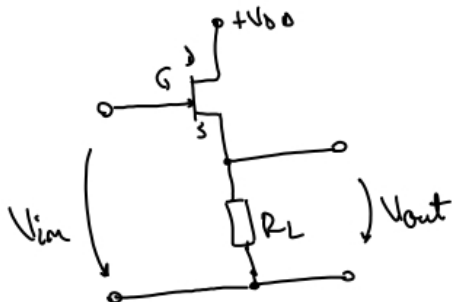


sin wave
 $\Delta \varphi = 180^\circ$

2) Poartă comună:



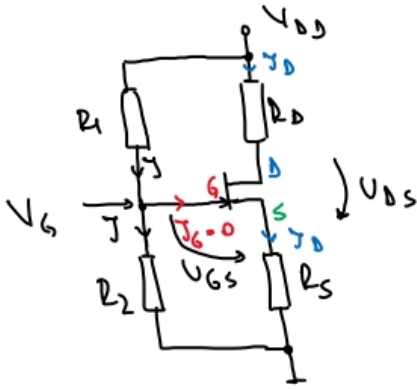
3) Drenă comună: "buffer"; "voltage follower"



$V_{out} = V_{in}$

Polarizarea JFET:

1) cu divizor de tensiune în poartă



Condiții practice

$$R_1, R_2 \rightarrow M \Omega$$

$$R_D, R_S \rightarrow k \Omega$$

$$V_{DD} = I_D (R_1 + R_2)$$

$$V_{DD} = I_D R_D + I_D R_S + V_{DS}$$

$$I_D R_S = V_{GS} + I_D R_S$$

71) Pentru circuitul de mai sus găsiți valorile rezistențelor astfel încât $I_D = 2 \text{ mA}$.

$$V_G = 5 \text{ V}$$

$$V_{DD} = 20 \text{ V}$$

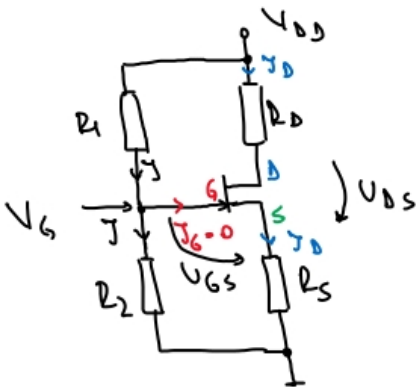
$$I_{DSS} = 4 \text{ mA}$$

$$V_T = -2 \text{ V}$$

$$R_D = 2.2 \text{ k} \Omega$$

$$R_1, R_2, R_S = ?$$

Determinați regiunea în care se află tranzistorul



$$V_G = 5 \text{ V}$$

$$V_{DD} = 20 \text{ V}$$

$$V_{DD} = I_D (R_1 + R_2)$$

$$V_G = I_D R_2$$

$$\frac{V_G}{V_{DD}} = \frac{I_D R_2}{I_D (R_1 + R_2)}$$

$$V_G (R_1 + R_2) = V_{DD} R_2$$

$$V_G R_1 + V_G R_2 = V_{DD} R_2$$

$$V_G R_1 = (V_{DD} - V_G) R_2$$

$$\frac{R_1}{R_2} = \frac{V_{DD} - V_G}{V_G} = \frac{20 - 5}{5} = \frac{15}{5} = 3$$

$$R_1 = 3 R_2$$

Alegem $R_2 = 1 \text{ M} \Omega \Rightarrow R_1 = 3 \text{ M} \Omega$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_T}\right)^2$$

$$2 \mu A = 4 \mu A \left(1 - \frac{V_{GS}}{-2}\right)^2$$

$$\frac{1}{2} = \left(1 + \frac{V_{GS}}{2}\right)^2$$

$$\frac{1}{\sqrt{2}} = 1 + \frac{V_{GS}}{2} \Leftrightarrow \frac{1}{\sqrt{2}} = \frac{2 + V_{GS}}{2}$$

$$\frac{2}{\sqrt{2}} = 2 + V_{GS} \Rightarrow$$

$$\Rightarrow V_{GS} = \frac{2}{\sqrt{2}} - 2 = -0.5857$$

$$V_{GS} \approx -0.59 V$$

$$V_G = V_{GS} + I_D R_S$$

$$5 V = -0.59 V + I_D R_S \Rightarrow I_D R_S = 5.59 V$$

$$R_S = \frac{5.59 V}{2 \mu A} = 2.795 k\Omega$$

$$R_S \approx 2.8 k\Omega$$

$$V_{DSSat} = V_{GS} - V_T$$

$$V_{GS} = -0.58 V$$

$$V_T = -2 V$$

$$\Rightarrow V_{DSSat} = -0.58 - (-2) = 1.42 V$$

$$V_{DD} = I_D R_D + V_{DS} + I_D R_S \Rightarrow$$

$$\Rightarrow V_{DS} = V_{DD} - I_D (R_D + R_S) = 20 V - 2 \mu A \cdot 5 k\Omega = 10 V$$

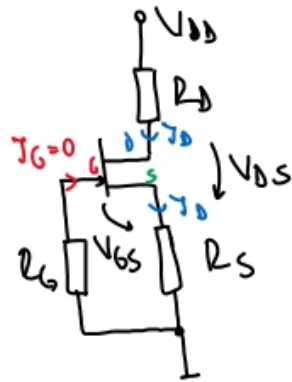
$$V_{DS} = 10 V$$

$$V_{DSSat} = 1.42 V$$

$$\Rightarrow V_{DS} > V_{DSSat} \Rightarrow$$

\Rightarrow transistorul este în
zona activă (de saturație)

1) polarizarea JFET cu poarta conectată la masă:



$$V_{DD} = I_D (R_D + R_S) + V_{DS}$$

$$I_D R_G = V_{GS} + I_D R_S$$

$$V_{GS} = -I_D R_S$$

92)

Pentru schema de mai sus determinați R_D astfel încât tranzistorul să lucreze în regiune de saturație.

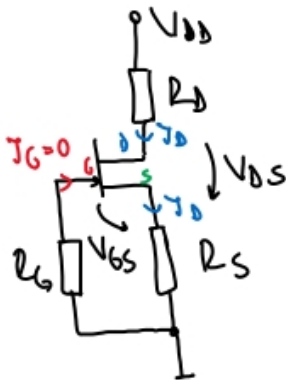
$$R_G = 1 \text{ M}\Omega$$

$$R_S = 250 \Omega$$

$$I_{DSS} = 9 \text{ mA}$$

$$V_T = -3 \text{ V}$$

$$V_{DD} = 16 \text{ V}$$



$$V_{GS} = -I_D R_S = -250 \cdot I_D$$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_T}\right)^2$$

$$I_D = 9 \times 10^{-3} \left(1 - \frac{-250 I_D}{-3}\right)^2$$

$$I_D = 9 \times 10^{-3} (1 - 83.33 I_D)^2$$

$$I_D = 9 \times 10^{-3} (1 - 166.67 I_D + 6943.85 I_D^2)$$

$$I_D = 9 \times 10^{-3} - 1.503 I_D + 62.495 I_D^2$$

$$62.495 I_D^2 - 2.503 I_D + 9 \times 10^{-3} = 0$$

$$I_D^2 - 0.04 I_D + 0.144 \times 10^{-3} = 0$$

$$\Delta = 0.04 \times 0.04 - 4 \times 0.144 \times 10^{-3} = 10.24 \times 10^{-4}$$

$$I_D = \frac{0.04 \pm \sqrt{10.24 \times 10^{-4}}}{2} = 0.02 \pm \frac{1}{2} \sqrt{1024} \times 10^{-2} =$$

$$= 0.02 \pm 0.016 \text{ A} = 20 \pm 16 \text{ mA}$$

1) Presupunem $I_D = 36 \text{ mA}$ ($I_{DSS} = 9 \text{ mA}$)

$I_D \gg I_{DSS} \Rightarrow ? , ? , ?$

$V_{GS} = -9 \text{ V} \ll V_T \Rightarrow I_D = 0$ dar $I_D = 36 \text{ mA} \Rightarrow ? , ? , ?$

2) Presupunem $I_D = 4 \text{ mA}$

$$V_{GS} = -250 \times 4 \times 10^{-3} = -1 \text{ V}$$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_T}\right)^2 \Rightarrow \frac{I_D}{I_{DSS}} = \left(1 - \frac{V_{GS}}{V_T}\right)^2$$

$$\frac{4}{9} = \left(1 - \frac{V_{GS}}{V_T}\right)^2 \Rightarrow \frac{2}{3} = 1 - \frac{V_{GS}}{-3}$$

$$\frac{2}{3} = 1 + \frac{V_{GS}}{3}$$

$$\frac{V_{GS}}{3} = -\frac{1}{3} \Rightarrow V_{GS} = -1 \text{ V}$$

$$V_{DSSat} = V_{GS} - V_T = -1 - (-3) = 2 \text{ V}$$

Pentru ca JFET să fie activ (saturație) $V_{DS} > V_{DSSat}$ sau $V_{DS} > 2 \text{ V}$

$$V_{DD} = I_D (R_D + R_S) + V_{DS}$$

$$V_{DS} = V_{DD} - I_D (R_D + R_S) > 2$$

$$V_{DD} - I_D R_D - I_D R_S > 2$$

$$-I_D R_D > 2 + I_D R_S - V_{DD}$$

$$R_D < -\frac{2}{I_D} - R_S + \frac{V_{DD}}{I_D}$$

$$R_D < -\frac{2}{4} \times 10^3 - 250 + \frac{16}{4} \times 10^3$$

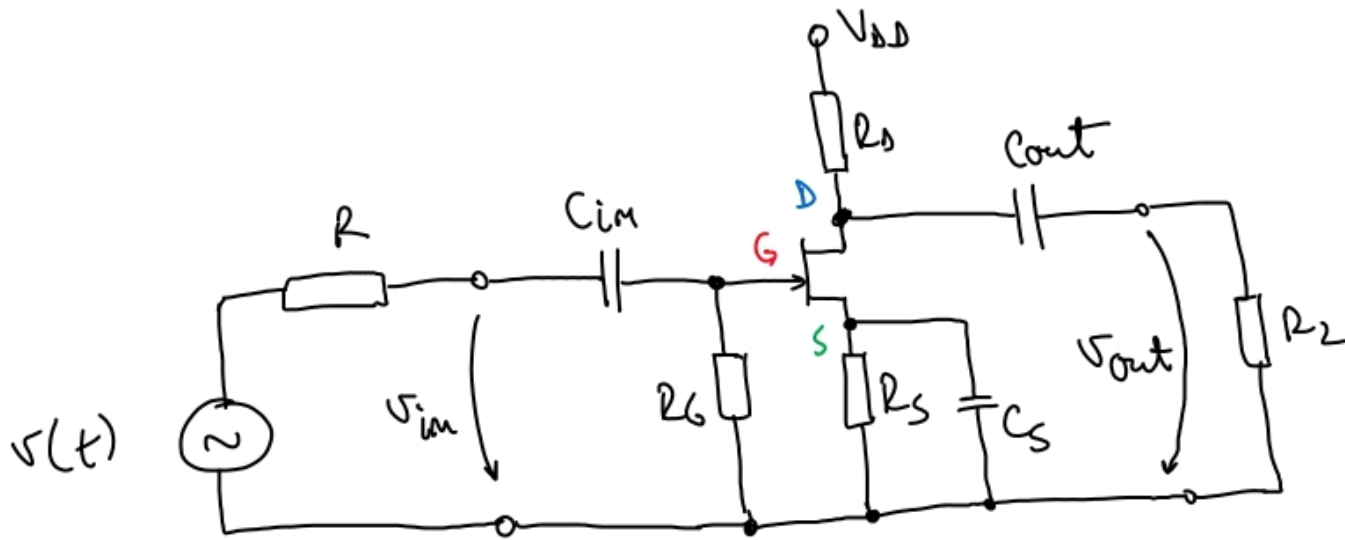
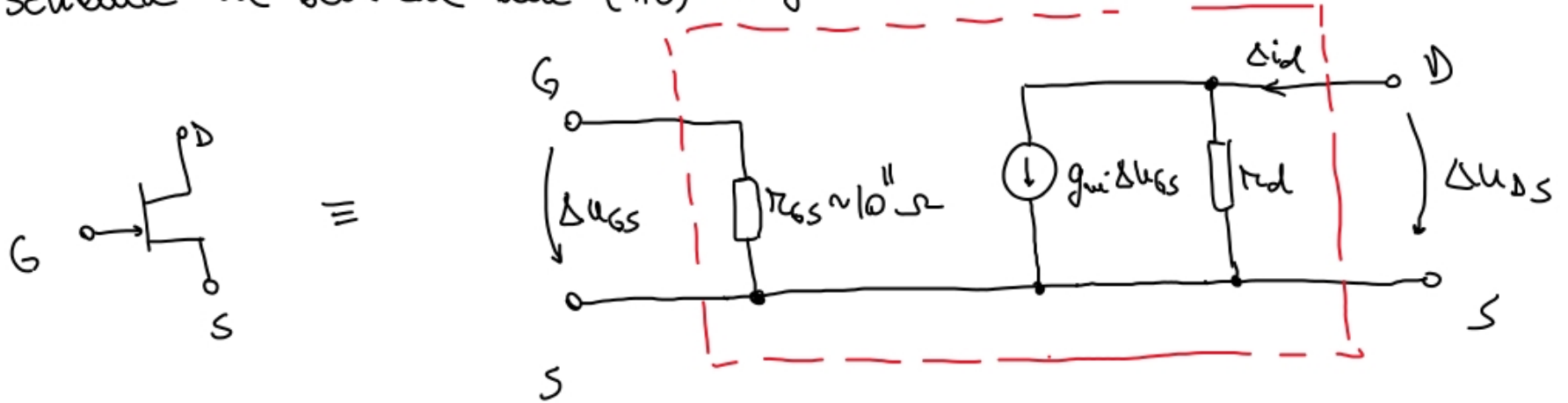
$$R_D < -500 - 250 + 4000$$

$$R_D < 3250 \Omega$$

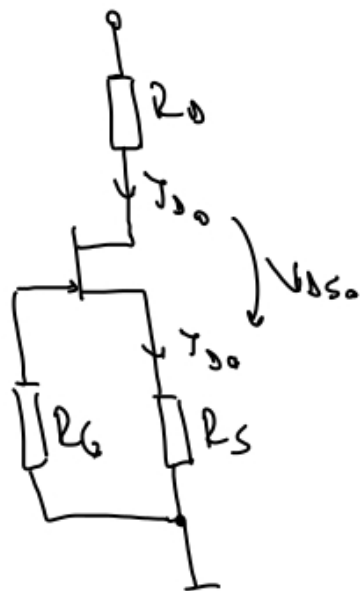
Pt. ca JFET să fie activ $\Rightarrow R_D < 3.25 \text{ k}\Omega$

Amplificatorul cu JFET conexiune surseă comună

Schema de semnal unic (AC) a JFET



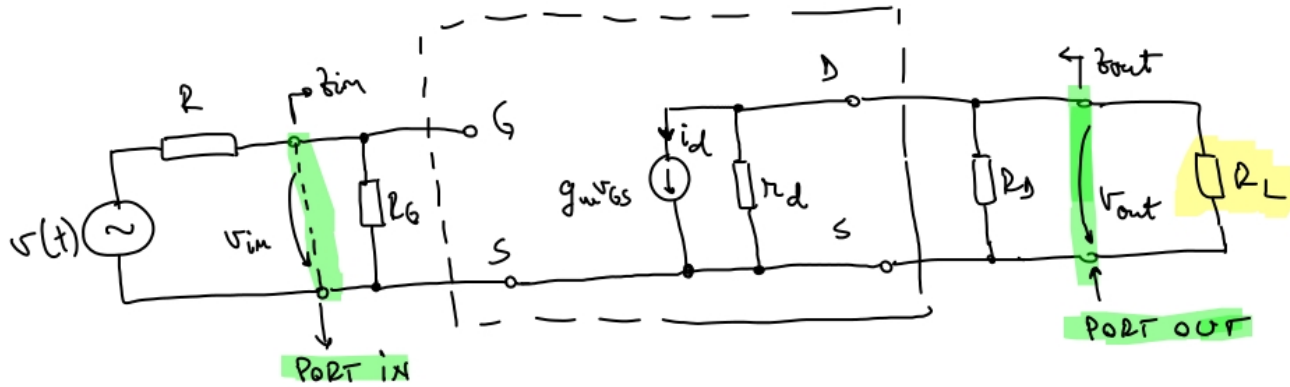
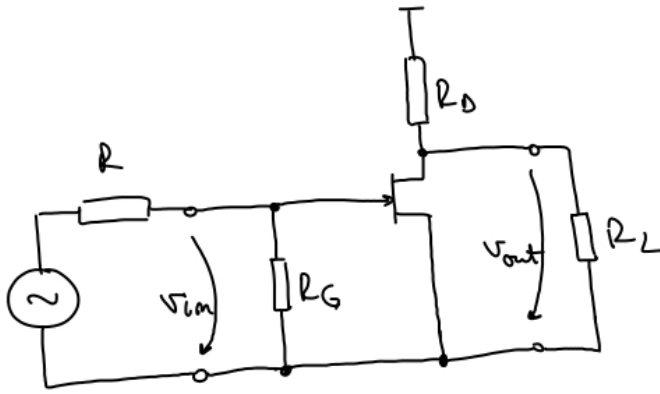
1) Schema echivalentă DC: => PSF



se cunoșc

I_{DSS}
 V_T

•) Schema echivalentă AC



$$Z_{in} = R_G = \frac{v_{in}}{i_{in}}$$

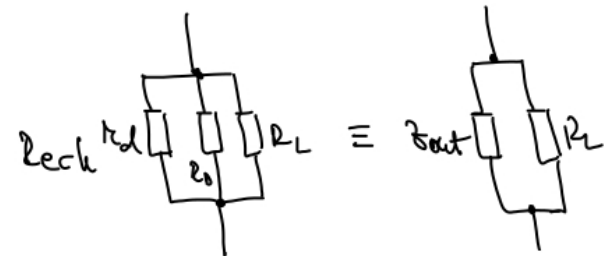
$$Z_{out} = r_d \parallel R_D$$

$$Z_{out} = \frac{1}{\frac{1}{r_d} + \frac{1}{R_D}} = \frac{r_d R_D}{r_d + R_D}$$

căştigul în tensiune:

$$A_v = \frac{v_{out}}{v_{in}} = \frac{-g_m v_{gs} \cdot R_{ech}}{v_{gs}}$$

$$A_v = -g_m R_{ech}$$



căştigul efectiv în tensiune

$$A_{vs} = \frac{v_{out}}{v}$$

$$v_{in} = \frac{R_G}{R + R_G} \cdot v \Rightarrow v = \frac{v_{in}}{\frac{R_G}{R + R_G}}$$

$$A_{vs} = \frac{v_{out}}{\frac{v_{in}}{\frac{R_G}{R + R_G}}} = \frac{v_{out}}{v_{in}} \cdot \frac{R_G}{R + R_G} = -g_m R_{ech} \cdot \frac{R_G}{R + R_G}$$